

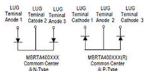
**Silicon Standard  
Recovery Diode**

$$V_{RRM} = 600 \text{ V} - 1600 \text{ V}$$

$$I_F = 400 \text{ A}$$

**Features**

- High Surge Capability
- Types up to 1600 V  $V_{RRM}$

**Heavy Three Tower Package**

**Maximum ratings, at  $T_J = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MSRTA400120(A)	MSRTA400140(A)	MSRTA400160(A)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		1200	1400	1600	V
RMS reverse voltage	$V_{RRMS}$		848	990	1131	V
DC blocking voltage	$V_{DC}$		1200	1400	1600	V
Continuous forward current	$I_F$	$T_C \leq 125^\circ\text{C}$	400	400	400	A
Surge non-repetitive forward current, Half Sine Wave	$I_{FSM}$	$T_C = 25^\circ\text{C}$ , $t_b = 8.3 \text{ ms}$	4150	4150	4150	A
Operating temperature	$T_J$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

**Electrical characteristics, at  $T_J = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MSRTA400120(A)	MSRTA400140(A)	MSRTA400160(A)	Unit
Diode forward voltage	$V_F$	$I_F = 400 \text{ A}$ , $T_J = 25^\circ\text{C}$	1.2	1.2	1.2	V
Reverse current	$I_R$	$V_R = 600 \text{ V}$ , $T_J = 25^\circ\text{C}$	25	25	25	$\mu\text{A}$
		$V_R = 600 \text{ V}$ , $T_J = 150^\circ\text{C}$	10	10	10	$\text{mA}$

**Thermal characteristics**

Thermal resistance, junction - case	$R_{\theta JC}$	0.14	0.14	0.14	$^\circ\text{C/W}$
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Figure .1- Typical Forward Characteristics

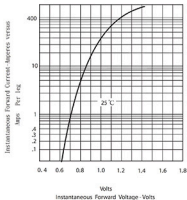


Figure.2 Forward Derating Curve

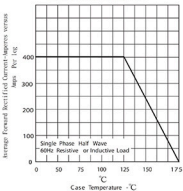


Figure.3 Peak Forward Surge Current

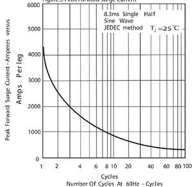


Figure 4 - Typical Reverse Characteristics

